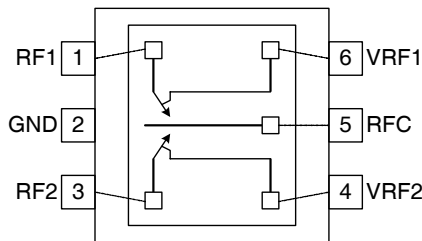




Features

- Low Frequency - 2.5GHz Operation
- Low Insertion Loss: 0.3dB at 1GHz
- High Isolation: 26dB at 1GHz
- Low Control Voltage: 2.6V to 5.0V
- Operation at 1.8V Control for Low Power Applications
- Excellent Harmonic Performance: -80dBc at 1GHz
- GaAs pHEMT Process



Functional Block Diagram

Applications

- Cellular Handset Applications
- Antenna Tuning Applications
- Multi-Mode GSM, WCDMA Applications
- IEEE802.11b/g WLAN Applications
- GSM/GPRS/EDGE Switch Applications
- Cellular Infrastructure Applications

Product Description

The RF1200 is a single-pole double-throw (SPDT) switch designed for general purpose switching applications which require very low insertion loss and high power handling capability. The RF1200 is ideally suited for battery operated applications requiring high performance switching with very low DC power consumption. The RF1200 features low insertion loss, low control voltage, high linearity, and very good harmonic characteristics. It is fabricated with 0.5µm GaAs pHEMT process, and is packaged in a very compact 2mmx2mm, 6-pin, leadless QFN package.

Ordering Information

RF1200 Broadband High Power SPDT Switch
RF1200PCBA-410 Fully Assembled Evaluation Board

Optimum Technology Matching® Applied

- | | | | |
|--------------------------------------|--------------------------------------|--|-----------------------------------|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input checked="" type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | <input type="checkbox"/> RF MEMS |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | <input type="checkbox"/> LDMOS |

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Absolute Maximum Ratings

| Parameter | Rating | Unit |
|--------------------------------------|-------------|------|
| Voltage | 7.0 | V |
| Maximum Input Power (0GHz to 2.5GHz) | +36 | dBm |
| Operating Temperature | -30 to +85 | °C |
| Storage Temperature | -35 to +100 | °C |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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| Parameter | Specification | | | Unit | Condition |
|---------------------------------------|---------------|------|------|------|--|
| | Min. | Typ. | Max. | | |
| | | | | | Temp = 25 °C, V _{CONTROL} = 2.65V |
| Insertion Loss | | | | | |
| RF>ANT | | 0.3 | 0.4 | dB | RF ON, 0.88GHz |
| RF>ANT | | 0.4 | 0.5 | dB | RF ON, 1.88GHz |
| RF>ANT | | 0.5 | 0.6 | dB | RF ON, 2.10GHz |
| RF>ANT | | 0.55 | 0.65 | dB | RF ON, 2.45GHz |
| RF>ANT Isolation | | | | | |
| RF>ANT | 26 | 27 | | dB | RF ON, 0.475GHz to 0.625GHz |
| RF>ANT | 25 | 26 | | dB | RF ON, 0.88GHz |
| RF>ANT | 21 | 22 | | dB | RF ON, 1.88GHz |
| RF>ANT | 19 | 20 | | dB | RF ON, 2.10GHz |
| RF>ANT | 17 | 18 | | dB | RF ON, 2.45GHz |
| 0.475GHz to 0.625GHz Harmonics | | | | | |
| Second Harmonic | | -114 | -103 | dBc | P _{IN} = 10dBm, 0.475GHz to 0.625GHz, 2f ₀ , V _{CONTROL} = 4.5V |
| Third Harmonic | | -132 | -105 | dBc | P _{IN} = 10dBm, 0.475GHz to 0.625GHz, 2f ₀ , V _{CONTROL} = 4.5V |
| 0.8GHz to 1GHz Harmonics | | | | | |
| Second Harmonic | | -80 | | dBc | P _{IN} = 34.5dBm, 0.88GHz, 2f ₀ |
| Third Harmonic | | -75 | | dBc | P _{IN} = 34.5dBm, 0.88GHz, 3f ₀ |
| 1.7GHz to 2.0GHz Harmonics | | | | | |
| Second Harmonic | | -80 | | dBc | P _{IN} = 31.5dBm, 1.9GHz, 2f ₀ |
| Third Harmonic | | -80 | | dBc | P _{IN} = 31.5dBm, 1.9GHz, 3f ₀ |
| 2.45GHz Harmonics | | | | | |
| Second Harmonic | | -90 | | dBc | P _{IN} = 31.5dBm, 1.9GHz, 2f ₀ |
| Third Harmonic | | -90 | | dBc | P _{IN} = 31.5dBm, 1.9GHz, 3f ₀ |
| IMD Due to Out-of-Band Blocker | | | | | |
| RF>ANT | | -105 | | dBm | P _{IN} = 20dBm @ 1950MHz, P _{BLOCK} = -15dBm @ 4090MHz |
| RF Port Return Loss | | | | | |
| RF>ANT | | 15 | | dB | 0.5GHz to 2.5GHz |

| Parameter | Specification | | | Unit | Condition |
|---|---------------|------|------|------|-----------|
| | Min. | Typ. | Max. | | |
| Input Power at 0.1dB Compression Point | | | | | |
| | 37 | | | dBm | 0.88GHz |
| | 34 | | | dBm | 1.88GHz |
| Switching Speed | | | | | |
| | | | 5 | us | |

Note: Parameters hold at 25°C and $V_{CONTROL} = 2.65V$.

Switch Control Settings

| | Control Signals | | Signal Paths | |
|----------------|-----------------|------|----------------------|---------|
| | VRF1 | VRF2 | RF1-RFC | RF2-RFC |
| Valid States | 1 | 0 | ON | OFF |
| | 0 | 1 | OFF | ON |
| Invalid States | 0 | 0 | Indeterminate State* | |
| | 1 | 1 | Indeterminate State* | |

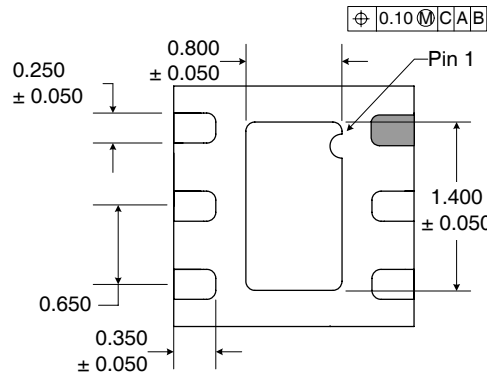
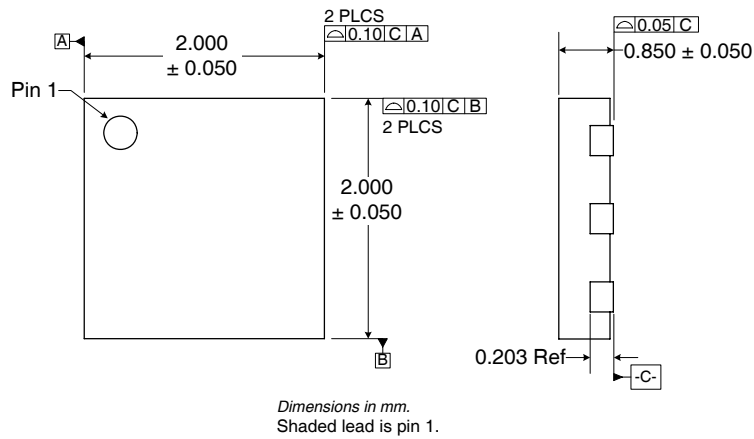
0: Logic level low, 0V~0.2V

1: Logic level high, 2.6V~5.0V

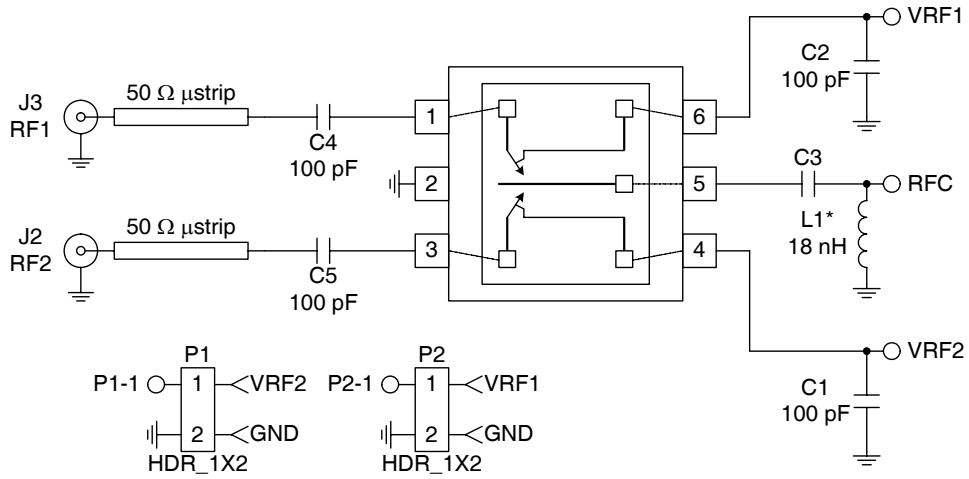
Note: In indeterminate states, both signal paths are ON with degraded performance.

| Pin | Function | Description | Interface Schematic |
|----------|----------|-----------------------|---------------------|
| 1 | RF1 | First RF connection. | |
| 2 | GND | Ground. | |
| 3 | RF2 | Second RF connection. | |
| 4 | VRF2 | Second RF control. | |
| 5 | RFC | Common RF connection. | |
| 6 | VRF1 | First RF control. | |
| Pkg Base | GND | | |

Package Drawing



Evaluation Board Schematic

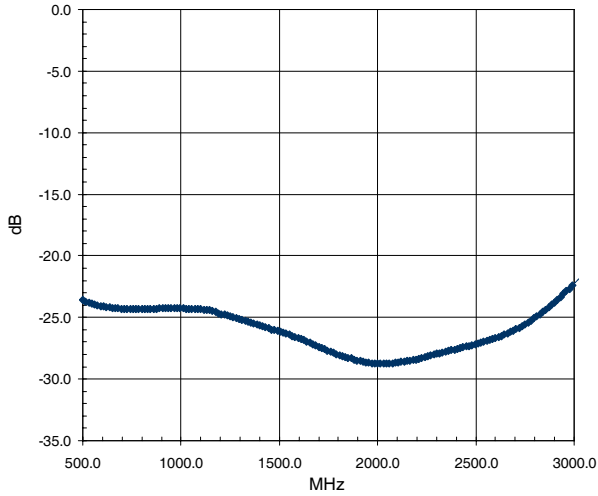


*L1 is optional for IEC61000-4-2 ESD protection.

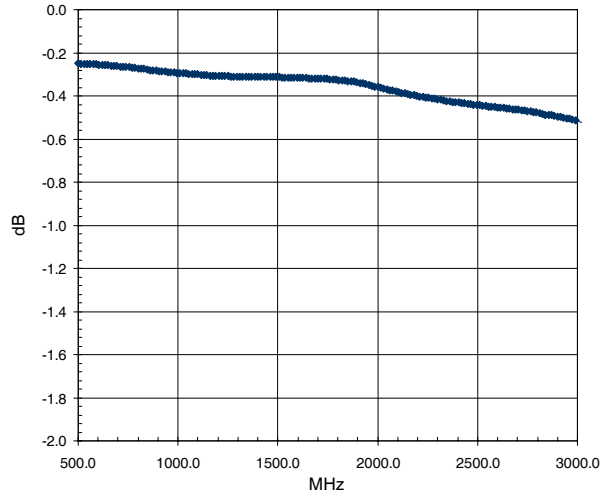
Typical Performance

Temp=25°C, V_{CONTROL} = 2.65V

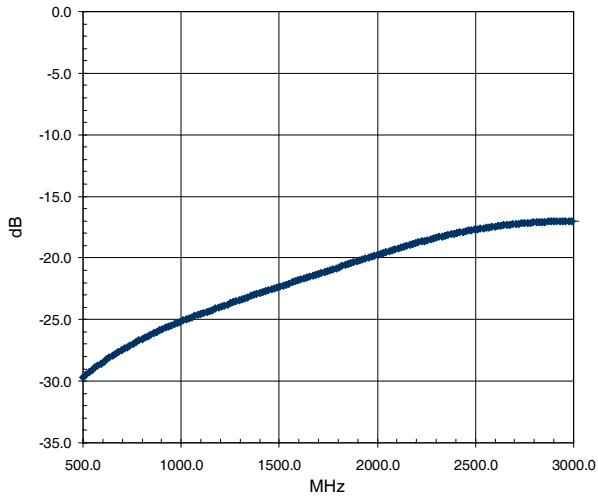
Return Loss



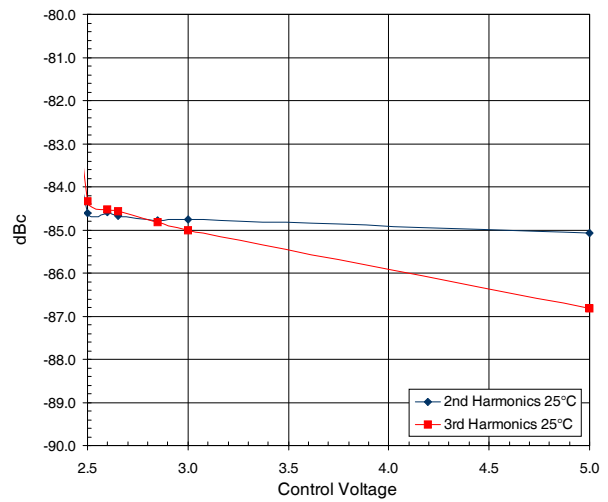
Insertion Loss

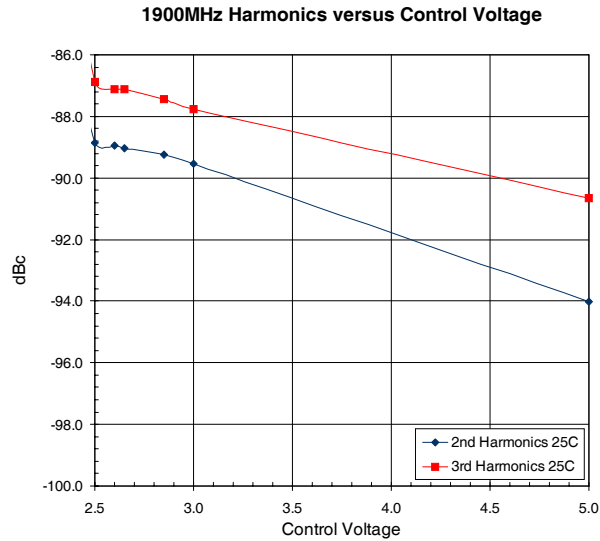


Isolation



900MHz Harmonics versus Control Voltage





RoHS* Banned Material Content

RoHS Compliant: Yes
 Package total weight in grams (g): 0.01
 Compliance Date Code: N/A
 Bill of Materials Revision: 1200240A.5
 Pb Free Category: e3

| Bill of Materials | Parts Per Million (PPM) | | | | | |
|-------------------|-------------------------|----|----|-------|-----|------|
| | Pb | Cd | Hg | Cr VI | PBB | PBDE |
| Die | 0 | 0 | 0 | 0 | 0 | 0 |
| Molding Compound | 0 | 0 | 0 | 0 | 0 | 0 |
| Lead Frame | 0 | 0 | 0 | 0 | 0 | 0 |
| Die Attach Epoxy | 0 | 0 | 0 | 0 | 0 | 0 |
| Wire | 0 | 0 | 0 | 0 | 0 | 0 |
| Solder Plating | 0 | 0 | 0 | 0 | 0 | 0 |

This RoHS banned material content declaration was prepared solely on information, including analytical data, provided to RFMD by its suppliers, and applies to the Bill of Materials (BOM) revision noted above.

* DIRECTIVE 2002/95/EC OF THE EUROPEAN PARLIAMENT AND OF THE COUNCIL of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

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